NEW PRODUCT

Features

- Low On-Resistance
  - 90 mΩ @ V_{GS} = 4.5V
  - 110 mΩ @ V_{GS} = 2.5V
  - 200 mΩ @ V_{GS} = 1.5V
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- ESD Protected Gate
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

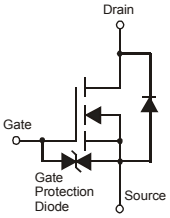
Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.008 grams (approximate)

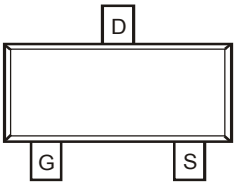
ESD PROTECTED TO 3kV

TOP VIEW

SOT-23



Equivalent Circuit



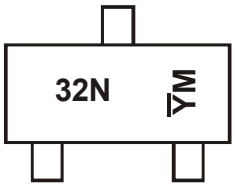
TOP VIEW

Ordering Information (Note 4)

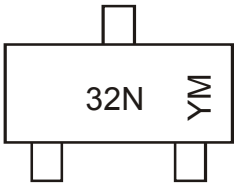
Part Number	Case	Packaging
DMN3200U-7	SOT-23	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

32N = Marking Code
YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
$\overline{Y}M$ = Date Code Marking for CAT (Chengdu Assembly/ Test site)
Y or $\overline{Y}$ = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	±8	V
Drain Current (Note 5)	I_D	2.2	A
Pulsed Drain Current (Note 5)	I_{DM}	9	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	650	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	192	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±5	μA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	0.45	—	1.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	62	90	mΩ	V_{GS} = 4.5V, I_D = 2.2A
			70	110		V_{GS} = 2.5V, I_D = 2A
			150	200		V_{GS} = 1.5V, I_D = 0.67A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	5	—	S	V_{DS} =5V, I_D = 2.2A
Diode Forward Voltage (Note 6)	V_{SD}	—	—	0.9	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	290	—	pF	V_{DS} = 10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	66	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	35	—	pF	

Notes: 5. Device mounted on FR-4 PCB, on minimum recommended pad layout on 2oz. Copper pads.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

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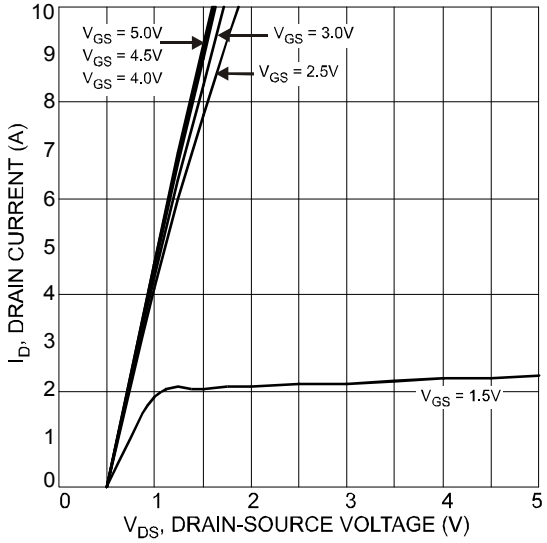

Fig.1 Typical Output Characteristic

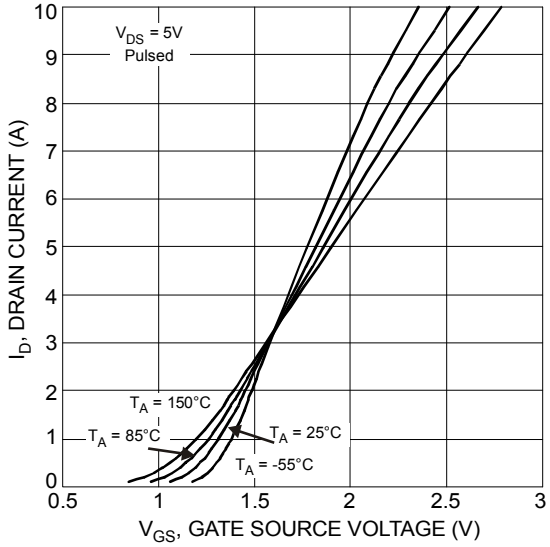

Fig. 2 Typical Transfer Characteristics

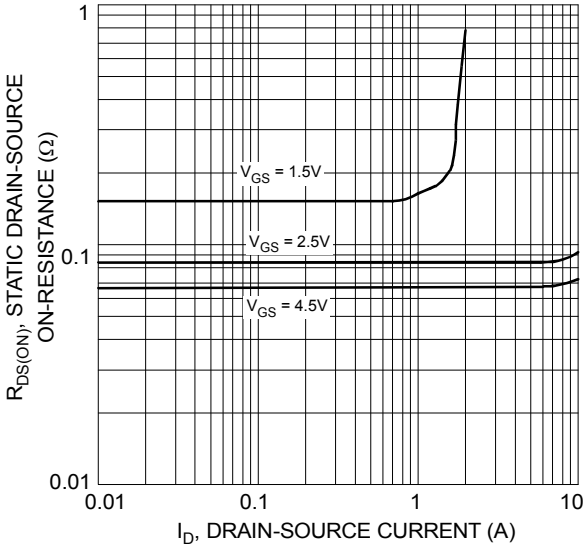

Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

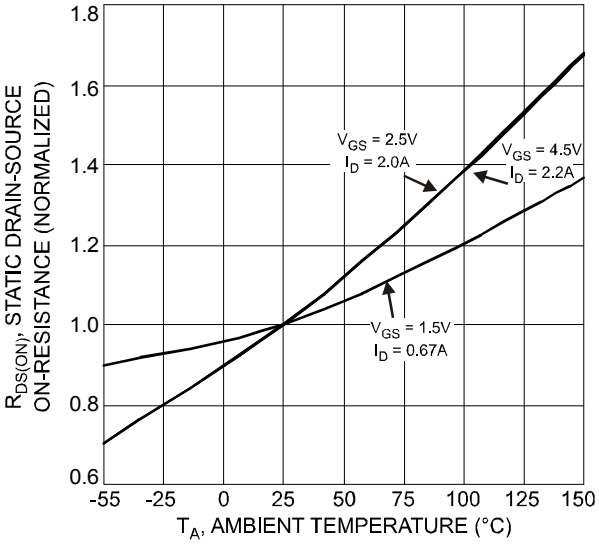

Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

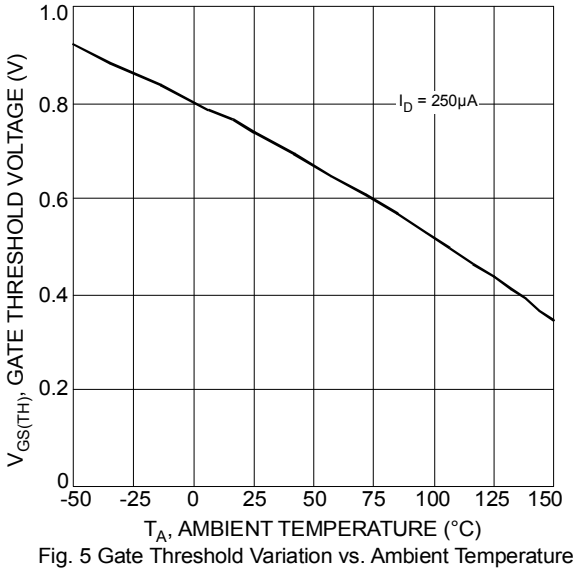

Fig. 5 Gate Threshold Variation vs. Ambient Temperature

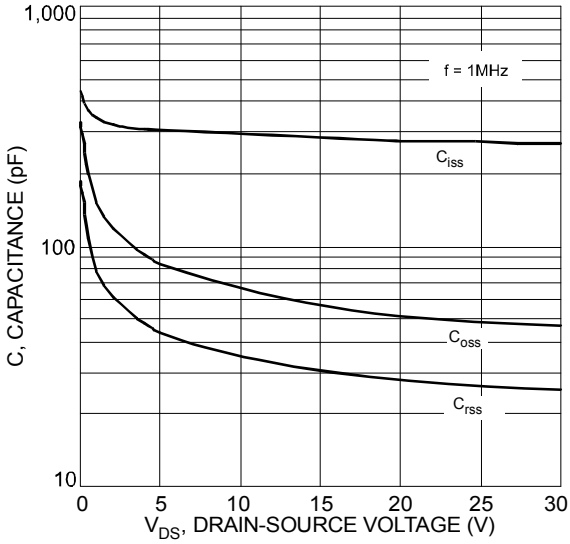

Fig. 6 Typical Total Capacitance

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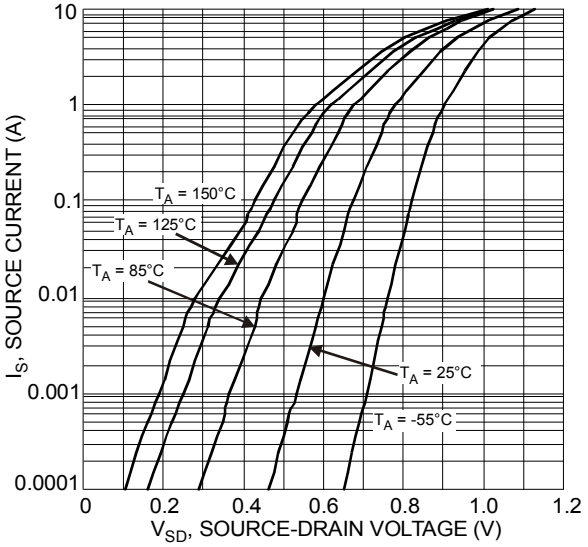
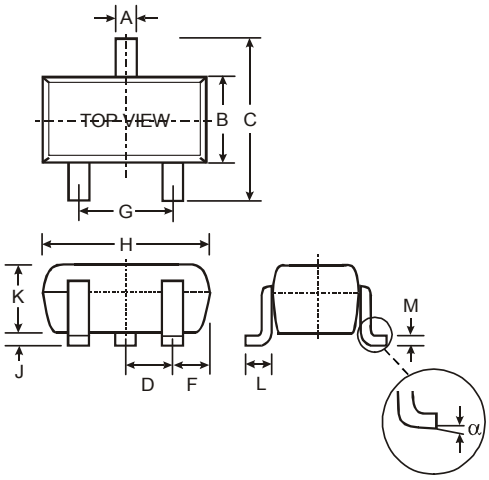


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Package Outline Dimensions

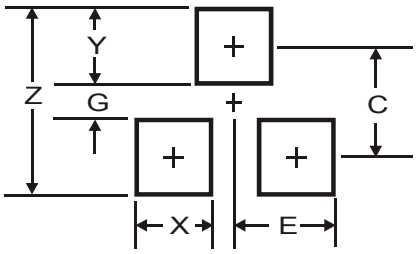
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23		
Dim	**Min**	**Max**
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
F	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Dimensions	Value (in mm)
Z	3.4
G	0.7
X	0.9
Y	1.4
C	2.0
E	0.9

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